

FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP  
225 Franklin Street, Boston, MA 02110  
Telephone: (617) 426-9180

MIT.9889  
ATTORNEY DOCKET NO.

10/603,712  
SERIAL NO.

APPLICANT: Lee et al.

GROUP: 281/5

FILING DATE: 06/25/2003

EXAMINER: Unknown

A. Wilson

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>OW</i>	AA	2002/0052084	05/02/2002	Fitzgerald	438	282	05/02/2002
	AB						
	AC						
	AD						
	AE						

**FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AF						
	AG						
	AH						

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
<i>OW</i>	AI	"Channel width dependence of mobility in Ge channel modulation-doped structures," Irisawa et al. <i>Jpn. J. Appl. Phys.</i> April 2001. Vol. 40.
<i>OW</i>	AJ	"Thermal stability of Ge channel modulation doped structures," Irisawa et al. <i>Journal of Crystal Growth</i> . 2001. Vol. 227-228. *
<i>OW</i>	AK	"Hall mobility enhancement caused by annealing of $\text{Si}_{0.2}\text{Ge}_{0.8}/\text{Si}_{0.7}\text{Ge}_{0.3}/\text{Si}(001)$ p-type modulation-doped heterostructures," Myronov et al. <i>Applied Physics Letters</i> . May 2002. Vol. 80, No. 19.
<i>OW</i>	AL	"Quantum mechanical modeling of the charge distribution in a $\text{Si}/\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ P-Channel MOSFET," Hargrove et al. <i>Proceedings of the 1994 IEEE International Electron Devices Meeting</i> , San Francisco, CA. December 1994.
<i>OW</i>	AM	"Characteristics and device design of Sub-100 nm strained Si N- and PMOSFETs," Rim et al. <i>Symposium on VLSI Technology Digest of Technical Papers</i> . 2002. *
<i>OW</i>	AN	"Enhanced performance of strained-Si MOSFETs on CMP SiGe Virtual Substrate," Sugii et al. <i>International Electron Devices Meeting 2001. IEDM. Technical Digest</i> . *
<i>OW</i>	AO	"SiGe-On-Insulator (SGOI): Substrate Preparation and MOSFET Fabrication for Electron Mobility Evaluation," Cheng et al. <i>IEEE International SOI Conference</i> . Durango, CO. October 2001.
<i>OW</i>	AP	"Ultrahigh room-temperature hole hall and effective mobility in $\text{Si}_{0.3}\text{Ge}_{0.7}/\text{Ge}/\text{Si}_{0.3}\text{Ge}_{0.7}$ heterostructures," Irisawa et al. <i>Applied Physics Letters</i> . July 2002. Vol. 81, No. 5.

EXAMINER

DATE CONSIDERED

EXAMINER:

Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

\* No month cited.